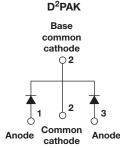
VS-HFA30TA60CSPbF

Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 2 x 15 A



www.vishay.com



PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
I _{F(AV)}	2 x 15 A							
V _R	600 V							
V _F at I _F	1.7 V							
t _{rr} (typ.)	19 ns							
T _J max.	150 °C							
Diode variation	Common cathode							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA30TA60CS is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A per leg continuous current, the VS-HFA30TA60CS is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30TA60CS is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		600	V					
Maximum continuous forward current	I	T _C = 100 °C	15						
per device	IF	$1^{\circ}_{\rm C} = 100^{\circ}_{\rm C}$	30	А					
Single pulse forward current	I _{FSM}		150	A					
Maximum repetitive forward current	I _{FRM}		60						
Maximum power dissipation	р	T _C = 25 °C	74	°C					
Maximum power dissipation	P _D	T _C = 100 °C	29	C					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	W					

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RoHS

COMPLIANT

HALOGEN

FREE

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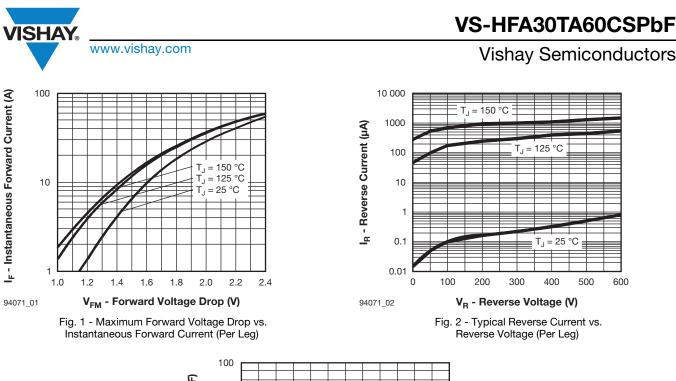
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ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-			
Maximum forward voltage		I _F = 15 A		-	1.3	1.7	V		
	V _{FM}	I _F = 30 A	See fig. 1	-	1.5	2.0			
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6			
Maximum reverse		$V_R = V_R$ rated	See fig. 0	-	1.0	10			
leakage current	I_{RM} T _J = 125 °C, V _R = 0.8 x V _R rated See fig. 2		See lig. 2	-	400	1000	μA		
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	25	50	pF		
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time See fig. 5, 10	t _{rr}	$I_F = 1.0 \text{ A}, \ dI_F/dt = 200$	A/μs, V _R = 30 V	-	19	-	ns		
	t _{rr1}	T _J = 25 °C		-	42	60			
	t _{rr2}	T _J = 125 °C		-	70	90			
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C	$I_{\rm F} = 15 \text{ A}$ $dI_{\rm F}/dt = 200 \text{ A}/\mu \text{s}$	-	4.0	6.0	A		
	I _{RRM2}	T _J = 125 °C		-	6.5	10			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	80	180			
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	220	450	no		
Peak rate of fall of recovery current during t _b	dl _{(rec)M} /dt1	T _J = 25 °C		-	188	-	A∕µs		
See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	A/µs		

THERMAL - MECHANICAL SPECIFICATIONS PER LEG										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Junction to case, single leg conducting	D		-	-	1.7					
Junction to case, both legs conducting	– R _{thJC}		-	-	0.85	K/W				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80					
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style D ² PAK		HFA30TA60CS						





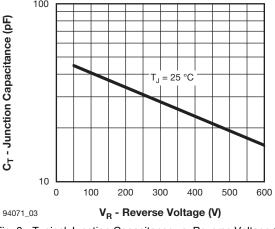
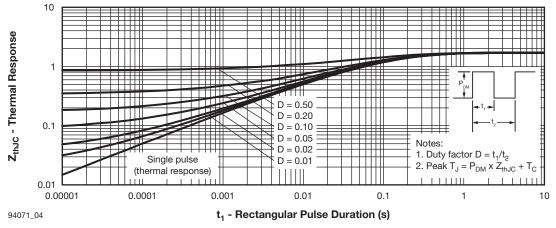


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)





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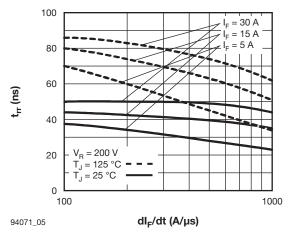


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

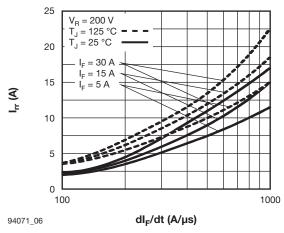


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)

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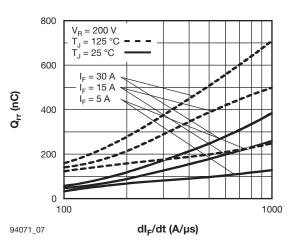


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

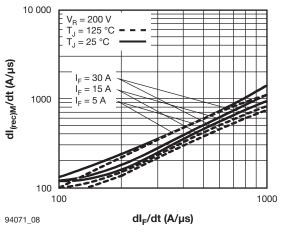


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

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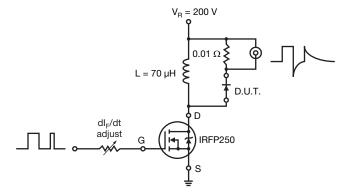
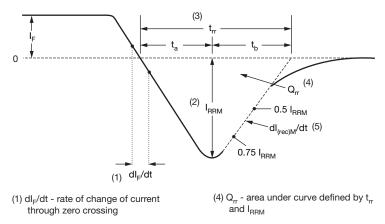


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5) $dI_{(rec)M}/dt$ peak rate of change of current during t_b portion of t_{rr}
- Fig. 10 Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Revision: 27-Aug-12

Device code	VS-	HF	Α	30	ТА	60	С	S	TRL	PbF	
	1	2	3	4	5	6	7	8	9	10	
	1 .		-	niconduo	ctors pro	oduct					
	드	-									
	3 ·	 Process designator: A = Electron irradiated 									
	4	- Current rating (30 = 30 A)									
	5	- Pac	kage ou	utline (T	A = TO-	220, 3 I	eads)				
	6	- Vol	age rati	ing (60 =	= 600 V))					
	7	- Circ	uit conf	iguratio	n (C = C	commor	n cathoo	le)			
	8	- S =	D ² PAK								
	9.	9 - • None = Tube									
		 TRL = Tape and reel (left oriented) 									
		• TI	RR = Ta	pe and	reel (rig	ht orien	ted)				
	10 ·	• • Pl	oF = Lea	ad (Pb)-	free						
		• P	= Lead	(Pb)-fre	e (for D ²	² PAK T	RR and	TRL)			

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95054						
Packaging information	www.vishay.com/doc?95032						

ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA30TA60CSPBF	50	1000	Antistatic plastic tube						
VS-HFA30TA60CSTRRP	800	800	13" diameter reel						
VS-HFA30TA60CSTRLP	800	800	13" diameter reel						

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VS-HFA30TA60CSPbF

Outline Dimensions

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D²PAK



Conforms to JEDEC outline D²PAK (SMD-220) в Pad layout (2)(3)A 11.00 MIN.-(E) F (0.43)ŧ (3) L1 4 (|(0.38)^{MIN.} (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З 0.15)^{0.01} Ľ L2 Ĥ ţ В В 2.32 MIN. (0.08) 2.64 (0.103) 2.41 (0.096) (3)Ċ 2 x b2 С View A - A 2 x h // ± 0.004 M B ⊕ 0.010 M A M B Base Plating (4) Metal 2 x e Н b1, b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 A1 Lead tip (b, b2) Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A" 3. - Anode

Rotated 90 °CW Scale: 8:1

SYMBOL	MILLIMETERS		INCHES		NOTES		HES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.		STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES			
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3		
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3		
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3		
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC			
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625			
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110			
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3		
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070			
c2	1.14	1.65	0.045	0.065			L3 0.25 BSC 0.010 BSC		BSC					
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208			

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

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DIMENSIONS in millimeters and inches



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